Vel Tech Multi Tech Dr.Rangarajan Dr.Sakunthala Engineering College

(An Autonomous Institution affiliated to Anna University)

Department of Electronics and Communication Engineering

PG M.E VLSI Design

Regulation 2019

Syllabus

Academic Year 2019-20

Cate	gory	Foundation Course					
Cou	rse code	192MA101					
Cou	rse Title	Graph Theory and	Optimization Techr	iques			
	Scheme and Credits						
Sem	ester –I	L	Т	Р	Credit	ts	
		4	0	0	4		
Un	it-1	BASIC	CONCEPTS IN GR	APH THEORY		12	
Com (state isom mant	mon fami ement onl orphism. I es. Digrap	ilies of graphs, deg y). Walk, trail and Representations of gr h - orientation, strong	gree sequence, hand path, connected grap aphs - adjacency and ply, weakly and unilat	shaking lemma, H h, distance, radius Incidence lists - ad erally connected dig	avel-Hakimi and diameter jacency and in raphs	theorem . Graph cidence	
Un	it-2		GRAPH ALGORI	THMS		12	
Tree	s, spanning	g trees, matrix tree th	eorem. Search algorit	hms - depth first sea	rch and bread	th first	
searc	h. spannin	g tree algorithm -Kru	iskal's and Prim's, sho	rtest path algorithm			
Unit-3 APPLICATION OF GRAPH ALGORITHMS 1					12		
Dijks chara maxi	stra's flow acterization mum flow	networks: flows and n of maximum flow r, augmenting path, ar	l cuts in networks, so Maxflow MM-cut nd FFEK - maximum	lution of the maxim Theorem (statement flow.	um flow prol only), algorit	blem - thms -	
Un	it-4		LINEAR PROGRA	MMING		12	
Form simp (east prob	nulation, s lex metho cost met lem.	implex method, two d. Transportation me thod, Vogel's appro	phase method, sim odel - initial basic fe ximation method, an	plex multipliers, du easible solution- nor nd optimum solutio	al and primal th-west corne on of transpo	, dual r rule, rtation	
Un	it-5	Ι	DYNAMIC PROGRA	AMMING		12	
Princ meth	ciple of op od of solu	ptimality, backward tion, shortest-route pr	and forward recursio oblem, Knapsack mo	n, calculus method del.	of solution, t	abular	
			References				
1	West D B	, Introduction to grap	oh Theory, Pearson Eo	lucation. New Delhi,	, 2018.		
2	Hamdy A	Taha, Operations Re	esearch: An Introducti	on, Pearson Education	on. New Delhi	, 2017.	
3	3 NarasinghDeo, Graph Theory: with applications to engineering and computer science, PHI Learning, 2017.					PHI	
4	Kambo N	S., Mathematical Province I.S., Mathematical Province International	ogramming Techniqu	es. East - West Press	, New Delhi. 2	2012	
5	Jonathan York, 200	L Gross and Jay Yell)6.	en, Graph Theory and	l its Applications, Ch	apman 8 Hall	, New	

Category	Programme core	Programme core					
Course code	192VL121	192VL121					
Course Title	MOS DEVICE PE	IYSICS					
		Scheme a	nd Credits				
	L	Т	Р	Cred	its		
	3	0	0	3			
Unit-1		MOS CAI	PACITORS		9		
Surface Potential: Accumulation, Depletion, and Inversion, Electrostatic Potential and Charge Distribution in Silicon, Capacitances in an MOS Structure, Polysilicon-Gate Work Function and Depletion Effects, MOS under Nonequilibrium and Gated Diodes, Charge in Silicon Dioxide and at the Silicon–Oxide Interface, Effect of Interface Traps and Oxide Charge on Device Characteristics, High-Field Effects, Impact Ionization and Avalanche Breakdown, Band-to-Band Tunneling, Tunneling into and through Silicon Dioxide, Injection of Hot Carriers from Silicon into Silicon Dioxide, High-Field Effects in Gated Diodes, Dielectric Breakdown9Unit-2MOSFET DEVICES9Long-Channel MOSFETs, Drain-Current Model, MOSFET I–V Characteristics, Subthreshold							
Channel Mobil MOSFETs, She Modulation, So Unit-3 MOSFET Scal Voltage, Thresl Effect on Three Length, Variou Physical Mear	Characteristics, Substrate Bias and Temperature Dependence of Threshold Voltage, MOSFET Channel Mobility, MOSFET Capacitances and Inversion-Layer Capacitance Effect, Short-Channel MOSFETs, Short-Channel Effect, Velocity Saturation and High-Field Transport Channel Length Modulation, Source–Drain Series Resistance, MOSFET Degradation and Breakdown at High Fields Unit-3 CMOS DEVICE DESIGN 9 MOSFET Scaling, Constant-Field Scaling, Generalized Scaling, Nonscaling Effects, Threshold Voltage, Threshold-Voltage Requirement, Channel Profile Design, Nonuniform Doping, Quantum Effect on Threshold Voltage, Discrete Dopant Effects on Threshold Voltage, MOSFET Channel Length, Various Definitions of Channel Length, Extraction of the Effective Channel Length,						
Measurements Unit-4	СМС	OS PERFORMANCI	E FACTORS		9		
Basic CMOS Circuit Elements, CMOS Inverters, CMOS NAND and NOR Gates, Inverter and NAND Layouts, Parasitic Elements, Source–Drain Resistance, Parasitic Capacitances, Gate Resistance, Interconnect R and C, Sensitivity of CMOS Delay to Device Parameters, Propagation Delay and Delay Equation, Delay Sensitivity to Channel Width, Length, and Gate Oxide Thickness, Sensitivity of Delay to Power-Supply Voltage and Threshold Voltage, Sensitivity of Delay to Parasitic Resistance and Capacitance, Delay of Two-Way NAND and Body Effect, Performance Factors of Advanced CMOS Devices, MOSFETs in RF Circuits, Effect of Transport Parameters on CMOS Performance, Low-Temperature CMOS Unit-5							
n–p–n Transist for Describing Current, Curre Transistor, Effe	ors, Basic Operation Bipolar Transistors, I ent Gains, Ideal I _C ect of Emitter and B	of a Bipolar Transist Ideal Current–Voltage –V _{CE} Characteristics ase Series Resistance	or, Modifying the S Characteristics, Co , Characteristics of es, Effect of Base–C	imple Diode llector Currer f a Typical Collector Vol	Theory nt, Base n–p–n tage on		

Collector Current, Collector Current Falloff at High Currents, Nonideal Base Current at Low Currents, Bipolar Device Models for Circuit and Time-Dependent Analyses Basic dc Model, Basic ac Model, Small-Signal Equivalent-Circuit Model, Emitter Diffusion Capacitance, Charge-Control Analysis, Breakdown Voltages, Common-Base Current Gain in the Presence of Base–Collector Junction Avalanche, Saturation Currents in a Transistor, Relation Between BV_{CEO} and BV_{CBO}.

	References						
1	BehzadRazavi, "Fundamentals of Microelectronics" Wiley Student Edition, 2nd Edition.						
2	J P Collinge, C A Collinge, "Physics of Semiconductor devices" Springer 2002 Edition.						
3	Yuan Taur and Tak H. Ning, "Fundamentals of Modern VLSI Devices", Cambridge University Press, Second Edition.						

Categ	ory	Programme core						
Cours	se code	192VL122						
Cours	se Title	Digital IC Design						
			Scheme a	nd Credits				
Seme	Semester –I L T P Credi							
		3	0	0	3			
Uni	it-1	OVERVIE	EW OF VLSI DESIGN	METHODOLOGY	7	9		
VLS	I design	process Architectu	ral design Logical des	sign, Physical design	- Layout sty	les - Full		
custo	m. Sem	icustom approaches.	Layout design rules: N	eed for design rules -	Layer repres	sentations		
- CM	IOS N-V	Vell / P-Well design	rules - Design rule back	grounder-Layer assig	nments SOI	rules.		
Uni	it-2		MOS INVERT	ER:		9		
Statio	c charac	teristics Resistive lo	ad inverter - Inverter w	vith n-type MOSFET	load CMOS	inverter -		
Trans	sient cha	aracteristics Delay tir	ne definitions, calculation	on of delay times, pov	wer analysis			
Uni	it-3		STATIC LOGIC D	ESIGN		9		
Statio	CMOS	Design Compleme	entary CMOS, Ratioed	logic, Pass transistor	and transmis	sion gate		
Dyna Disto	thility (AOS logic CMC	S logic - Recharged c	lomino logic Static	Sequential	circuits -		
Dista	иоппцу, (н л			DESICN		0		
Dyng	mic sec	mantial circuits Dea	udo static latch Dyna	nic two phase FE	locked CM	9 OS latch		
NOR	A CMO	S logic. TSPCL logi	c.	ine two phase 11, C	IOCKCU- CIVI	OS laten,		
Uni	it-5	VI	SI BUILDING BLOC	KS DESIGN		9		
Adde	ers, Shif	ters, Arithmetic log	ic unit design Multipli	ers-Array, Carry Sav	e multiplier.	Wallace		
tree,	Booth's	algorithm, Modifie	d Booths Algorithm. l	Designing Memory a	and Array S	tructures-		
Mem	ory peri	pheral circuit.						
			References					
1	Jan M.	Rabaey, Anantha Cha	andrakasan, BorivojeNi	kolic, 'Digital Integra	ated Circuits	, Pearson		
	Educati	ion India, second edi	tion, 2016.		•	1 • 1		
2	Sung-N Design	10 Kang and Yusu Fourth Edition Tate	t Leblebici, CMOS D McGraw-Hill 2014	ligital Integrated Cir	cuits - Ana	lysis and		
	Neil H F Weste David Harris 'CMOS VI SI Design: A circuits and systems							
3	perspec	ctive'Pearson, 4th edi	tion 2015.	6		5		
4	Douglas	A Pucknell Kamran Es	hraghian, 'Basic VLSI Desig	gn. PHI learning, New D	elhi. 2011.			
5	Saida M	A Sait and youssef,	'VLSI Physical Design	Automation: Theory	y and Practic	e, World		
3	Scienti	fic Publishing Compa	any, 1999.					

Catego	orv	Programme core				
Course	o oodo	1020/122				
Cours		192VL125				
Cours	e Title	Designing with F	PGAs			
			Scheme	e and Credits		
Semes	ter –I	L	Т	Р	Credits	
		3	0	0	3	
Unit	-1	I	Introduction to	o FPGA		9
XILIN	X 3000 s	series FPGAs, XILI	NX 4000 series FPC	GAs, Designing with	n FPGAs, Designi	ing with
FPGAs	s using O	ne Hot Assignment,	Altera CPLDs, Alte	era FLEX 10K serie	s CPLDs.	
Unit-	2	D	igital Logic Design	using VHDL		9
Variab	les, Sign	als, Constants, Arra	ys, VHDL Operator	s, Functions, Procee	lures, Packages, L	ibraries
VHDL	descript	ion of Combination	al Networks, Model	ing flip flops using	VHDL Processes	, VHDL
Model	s Combi	national Networks,	Compilation and S	Simulation of VHD	DL Code, VHDL	Models
Sequer	ntial Mac	hine.				1
Unit-	3		Testing			9
Testing	g Combir	national Logic, Testi	ng Sequential Logic	, Scan Testing, Bou	Indary Scan, BIST	
Unit-	4	Synthesis	of Combinational	and Sequential Log	gic	9
Introd	uction t	o Synthesis,Combi	national Logic,Sequ	uential Logic, three	state devices a	nd bus
interfa	ace, Sequ	ential with flip flop	s, explicit state macl	hine, Registered log	ic, state encoding,	,Implicit
state n	nachine,	Registers, Counters	, Resets, Gated cloo	cks, Clock enables,	Anticipating the	results,
Loops						[
Unit-	5		ControllerandDS	SPDesign		9
RISC S	SPM Pro	cessor, RISC SPM	ALU, RISC SPM C	Controller, Static RA	AM memory, a sin	mplified
486 Bi	us Model	l, interfacing memo	ry to a micro proce	ssor Bus, UART. I	OSP blocks- FIR	and IIR
filters.	filters.					
	References					
1	Charles	H. Roth, 'Digital sys	stem design using V	HDL. Thomson, 20	14	
2	Michael	D Clienti 'Advance	d Digital Design wi	th Verilog HDL Pea	arson education. 2	005.
3	Morris I Education	Mano M, Charles R on, 2015.	Kime, logic and Co	mputer Design Fund	lamentals, Pearson	n

Catego	ory	Programme core				
Course	e code	192VL124				
Course	e Title	Low Power VLS	I Design			
			8	cheme and Credits		
Semest	ter –I	L	Т	Р	Credits	
		3	0	0	3	
Unit-	1	PO	WER DISSI	PATION IN CMOS		9
Physics power of Power,	s of powe consump Circuit 7	er dissipation in CM tion – Static Power Fechniques For Lea	IOS FET devic Dissipation, A kage Power Re	es – Hierarchy of limits ctive Power Dissipation eduction - Basic princip	s of power – Source 1 - Designing for La le of low power des	es of ow sign.
Unit-	2		POWER OF	TIMIZATION		9
Adders Adders perforn	Archited -Types nance co	ctures-BiCMOS ad Of Multiplier Archi mparison	ders - Low Vol tectures, Braur	tage Low Power Design , Booth and Wallace Tr	ard Adder Cells, Cl 1 Techniques, Curre ree Multipliers and	ent Mode their
Unit-	3	DESIGN	OF LOW PO	WER CMOS CIRCU	ITS	9
low vol clock –	ltage low	v power static Rand	om access and	dynamic Random acces	s memories $-\log \frac{1}{2}$	power
Unit-	4	eu teeninques sp	POWER E	STIMATION		9
Power	Estimatio	on techniques – log	ic power estim	ation – Simulation pow	er analysis –Probab	oilistic
power a	analysis. 5	SOFT	WARF DESIG	N FOR LOW POWF	R	9
Source	s of softv	ware power dissipat	ion, software p	ower estimation, softwa	are power optimiza	tions,
codesig	gn for lov	w power	ŗ	- · · · · · · · · · · · · · · · · · · ·	I I I I I I I I I I I I I I I I I I I	7
			Refe	rences		
1	Gary Yea	p, "Practical low pov	ver digital VLSI d	esign", Kluwer, 1998		
2	Kaushik	Roy and S.C.Prasa	id, "Low powe	r CMOS VLSI circuit d	esign", Wiley, 200	0.
3	Kiat-send Yeo, Kaushik Roy "Low-Voltage, Low-power VLSI Subsystem", Tata McGraw- Hill, 2009					
4	Abdelati	fBelaouar, Mohameo	l.I.Elmasry, "Low	power digital VLSI design	n", Kluwer, 1995.	
5	A.P.Char	ndrasekaran and R.W	.Broadersen, "Lo	ow power digital CMOS de	esign", Kluwer,1995.	
6	Dimitrios	Soudris, C.Pignet, Co	ostas Goutis,"De	signing CMOS Circuits for	Low Power"Kluwer,	2002.
7	James B inc. 2001	.Kulo, Shih-Chia Lin, L	"Low voltage SC	I CMOS VLSI devices and	Circuits", John Wiley	and sons,
8	J.B.Kulo	and J.H Lou, "Low vo	ltage CMOS VLS	Circuits", Wiley 1999.		

Categ	ory	Programme core						
Cours	se code	192VL125						
Cours	se Title	Analog VLSI Circ	Analog VLSI Circuits					
	Scheme and Credits							
Semes	ster –II	L	Т	Р	Credi	its		
		4	0	0	4			
Unit	-1	ANALO	G CIRCUIT BUILI	DING BLOCKS		12		
Switch Comp gate.	nes. Acti arator. M	ve resistors. Currer ultiplier. Single stag	nt sources and sink e amplifiers - Comn	s. Current mirrors non source, Commo	voltage rei on drain and	ferences. common		
Unit	-2	DI	FFERENTIAL AMI	PLIFIERS		12		
MOS amplif op-am	inverting fiers - Qua p, single s	amplifier - Improv alitative and Quantita stage amplifier, comr	ing performance of ative Analysis, Chara- non mode feedback n	inverting amplifier cterization of Op-Ar etwork,Gilbert cell.	, CMOS dif np , CMOS t	fferential wo stage		
Unit	-3	L	AYOUT AND PACE	KAGING		12		
CMOS	S design r	ules –antenna effect,	analog layout technic	ques –Multi finger tr	ansistor, Syn	nmetry –		
Unit	-4	DATA	CONVERTER FUN	DAMENTALS		12		
Ideal	A/D and	D/A converters, Qu	antization noise, Sig	ned codes, Performa	ance limitatio	ons. D/A		
AND D/A a	A/D COl	NVERTERS:D/A co	nverter : Current sca	ling, Voltage scalin	g and Charge	e scaling		
Unit	-5	-Senar D/A converte	PHASE LOCKED I	COOPS	onventers	12		
Op-an	nps with	output stage, Folde	ed Cascode op-amp,	Transconductance	Amplifier-No	oise and		
Distor	tion in Ar	nplifiersPhase Dete	ctor-Voltage Controll	ed Oscillator-Loop I	Filter.			
			References					
1	Phillip A 2012.	llen and Douglas Ho	lberg. 'CMOS Analog	Circuit Design, Oxf	ord Universit	y Press,		
2	Jacob Ba	ker, -CMOS, Circuit	Design Layout and S	imulation', Wiley- IE	EEE Press, 20	11.		
3	BehzadRazavi ,DESIGN OF ANALOG CMOS INTEGRATED CIRCUITS, McGraw- Hill,2002							
4	Randall I and Digit	L Geiger, Phillip E A al Circuits'. McGraw	llen and Noel R Sooti HA International Ed	er, 'VLSI Design Teo ition, 2010.	chniques for A	Analog		
5	David A	avid A Johns and Ken Martin, 'Analog Integrated Circuit Design', John Wiley and Sons, 08.						
	2000.							
6	Benhard	hardRazavi, 'Data Converters', Kluwer Publishers, 2005.						

Catego	ory	Programme core	Programme core				
Course	e code	192VL12A					
Course Title		VLSI Design La	boratory				
			Sch	neme and Credits			
Semester –I		L	Т	Р	Credits		
		0	0	4	2		
1	Study of	of MOS and Inverte	er characteristics				
2	Design	of static and dynamic	nic digital circui	ts			
3	Design	of Memories with	Peripherals				
4	4 Model parameter extraction for diode, BJT, MOSFET						
5	Layout	generation from so	chematics				

Catego	ory	Mandatory Course				
Course	e code	192HS10A				
Course	Title	ENGLISH FOR	RESEARCH	PAPER WRITING		
			So	cheme and Credits		
Semest	er –I	L	Т	Р	Credits	
		0	0	**	Grade	
1	Planning and preparation, word order, breaking up of long sentences, structuring paragraphs and sentences, being concise and removing redundancy, avoiding ambiguity and vagueness, clarifying who did what, highlighting the findings, hedging and criticising, paraphrasing and placiarism (15)					
2	Section discuss	is of a paper - Abst ions, conclusions, a	ract, introduction acknowledgeme	on, review of the literatuents, references and the	re, methods, results and final check. (10)	
3	Key sk results	ills needed to write and discussions, an	title, abstract, i d conclusions of	introduction, review of of a research paper. (20)	the literature, methods,	
4	Use of the first	appropriate phrases t- time submission.	s to ensure the 1 (15)	research paper is as goo	d as it could possibly be	
REFEI	RENCE	S				
1	Adrian Heidell	Wallwork, "Englis berg London, 2011	h for Writing R	Research Papers", Sprin	ger New York Dordrecht	
2	Goldbo	ort R., "Writing for	Science", Yale	University Press, 2006		
3	Day R.	, "How to Write an	d Publish a Sci	entific Paper", Cambrid	ge University Press, 2006	
4	Highma Book, 1	an N., "Handbook 1998.	of Writing for t	he Mathematical Science	ces", SIAM, Highman's	

SEMESTER II

			SEMESTERI			
Cate	gory	Programme core				
Course	e code	192VL221				
Course	Course Title VLSI Testing					
			Scheme a	nd Credits		
Semest	ter –II	L	Т	Р	Credi	ts
		3	0	0	3	
Unit-1	L		Faults in Logic Ci	rcuits		9
Stuck-a	t Fault, I	Bridging Faults, Dela	y Fault, Breaks, Stuck	-on and Stuck-Open	Faults,	
Control	lability a	and Observability, U	ndetectable Faults, Eq	uivalent Faults, Tem	porary Faults.	
Unit-2	2	Fa	ult Detection in Log	ic Circuits.		9
Truth T	able and	Fault Matrix, Path	Sensitization, D-Algo	orithm, PODEM, FA	N, Delay Faul	t
Detectio	on, Desig	gning Checking Exp	eriments, Test Genera	tion Using the Circuit	it Structure and	d the
State Ta	able.					
Unit-3	3	Design For Testability				9
Ad Hoc	Technic	ques, Scan-Path Tec	hnique for Testable Se	equential Circuit Des	ign, Level-Se	nsitive
Scan De	esign, Cl	ocked Hazard-Free I	Latches, Double-Latch	and Single-Latch L	SSD, Random	Access
Scan Te	chnique	, Partial Scan, Testal	ole Sequential Circuit	Design Using Nonsc	an Technique	s,
Crossch	ieck, Bo	undary Scan.				
Unit-4	1		Built-in Self-T	est		9
Exhausti	ive Testir	ng, Pseudoexhaustive	Pattern Generation, Pseu	udorandom Pattern Ge	nerator, Determ	inistic
Testing,	Test Patt	ern Generation for BIS	ST, Transition Count, Sy	ndrome Checking, Sig	gnature Analysi	.S
Unit-5	5		Fault Diagnos	is		9
Logical	Level D	Diagnosis, basic conc	epts, FaultDictionary,	Guided Probe Testin	ng, Diagnosis	by UUT
reductio	on – Fau	It Diagnosis for Cor	nbinational Circuits. I	Expert systems for D	Diagnosis, effe	ct cause
analysis	5.					
			References			
1	P.K. La 2008.	ala, "An Introductio	n to Logic Circuit Te	esting", Morgan and	Claypool Pul	blishers,
2	M.Abra	amovici, M.A.Breue	r and A.D. Friedman	, "Digital systems a	nd Testable I	Design",
۷	JaicoPu	blishing House, 200	2.			
3	M.L.Bı	ishnell and V.D.Ag	rawal, "Essentials of	Electronic Testing	for Digital, I	Memory
5	andMix	edSignal VLSI Circ	uits", Kluwer Academ	ic Publishers, 2002.		
4	A.L.Cr	ouch, "Design Test	t for Digital IC"s a	nd Embedded Cor	e Systems",	Prentice
	HallInt	International, 2002.				

Ca	tegory	,	Programme core				
Cou	rse coo	le	192VL222				
Cour	rse Tit	le	Computer Aided I	Design for VLSI Syst	ems		
				Scheme a	nd Credits		
Seme	ester –	II	L	Т	Р	Cred	its
			3	0	0	3	
Uni	t-1			ALGORITHN	1		9
VLSI	Desig	n cy	cle - Role of CAD t	ools in the VLSI Desi	gn process data stru	ctures and alg	gorithms:
Comp	olexity	of a	Igorithms, dynamic	programming, Integer	linear programming	, Genetic algo	orithm.
Uni	t-2			SYNTHESIS			9
Simul princi	lated A	nne	aling. Logic synthes	is - two level synthesi	s. Binary decision d	iagrams, and	ROBDD
Unit	t-3		PHYS	SICAL DESIGN AU	ΓΟΜΑΤΙΟΝ		9
Partit	ioning	- K	, FM algorithms, P	acement - Simulation	based algorithms -	Simulated Ar	nealing.
Force Algor	Direct Tithm (ted A Clus	Algorithm. Partitioniter Growth Algorith	ng based algorithms- m Floor planning -	Breuer's Algorithm. slicing floor plan C	Terminal pro onstraint Bas	pagation ed Floor
Plann	ing. In	tege	r Program Based Flo	oor Planning -Pin Assi	gnment		
Uni	t-4			ROUTING			9
Grid tree b Chan	routing based nel Ro	g - N Algo uting	Maze Rowing Algorit prithms, detailed ro g, Switch Box Routin	thms. Global routing outing - Left Edge a ng algorithms- over th	, Shortest Path Base algorithm. Dog-Leg e cell routing, Clock	d Algorithms Algorithm Routing	, Steiner Greedy
Uni	t-5		LAYOUT	SYNTHESIS AND	OPTIMIZATION		9
Layou Comp	ut gene	erati - or	on and Optimization the dimensional and t	n of standard cell lay wo dimensional comp	out, gate matrix lay action	yout and PLA	A Layout
	References						
1	1 Sabih H Gerez, 'Algorithms for VLSI Design Automation John Wiley & Sons. 2008.						
2	Nave 2012	edSl	nerwani, Algorithms	for VLSI Physical De	esign Automation, 3/	e,Kluwer Aca	ademic,
3	Sait S	S M	and Youssef H. 'VLS	SI Physical Design Au	tomation World Sci	entific, 2004.	
4	Mich	ell C	B D, 'Synthesis and C	Optimization of Digita	l Circuits. Tata McG	Fraw Hill, 200	13

Category		Programme core				
Cour	se code	192VL223				
Cour	se Title	Hardware Verifica	ation Techniques			
			Scheme a	nd Credits		
Seme	ster –II	L	Т	Р	Cred	its
		4	0	0	4	
Unit	-1	VER	IFICATION TECH	NOLOGIES		12
Import Verific Reuse	tance of cation A _l - Linting	Verification - Record oproaches Timing Ver s-Simulation	nvergence Model Therification Testing Ve	ne Human Factor For rsus Verification De	ormal and Fuestign and Ver	inctional rification
Unit	-2		TOOLS			12
Third Functi Verific	Party M onal Co cation - V	Iodels Verification verage-Issue Trackir Verification strategies	Intellectual Property ng - Metrics - Role	- Waveform View e of the Verification	wers Code (on Plan - L	Coverage evels of
Unit	-3	1	HIGH-LEVEL MOD	DELING		12
High-I Orient	Level Ve	ersus RTL Thinking	Structure of High-L	evel Code - Data	Abstraction -	Object-
Unit	-4	<u></u>	TEST CASE GENER	RATION	51110y 1550005.	12
Simple Transa	e Stimulu	us, Simple Output, Co vel Interface - Verific	omplex Stimulus,Bus- ation Harness -	Functional Models -	· Response M	onitors -
Unit	-5	ARC	CHITECTING TEST	BENCHES		12
Design Level	n Configu Verificat	aration- Self Checkin ion Harnesses - Trans	g - Test benches, Dire action Level Models,	ected Stimulus, Rand Managing Simulatic	lom Stimulus ons-Regressio	s, System
			References			
1	Janick I	Bergeron, 'Writing Te	st Benches Using Sys	tem Verilog", Spring	ger 1' st Editio	on, 2009.
2	Chris S bench I	pear. Greg Tumbush. anguage Features' Sp	'System Verilog for V pringer 3rd edition, 20	Verification - A Guio 12.	de to learning	the Test
3	KropfT	, "Introduction to For	mal Hardware Verific	ation, Springer Verla	ag. 2010.	
4	Mark G	lasser, 'Open Verifica	ation Methodology Co	ookbook', Springer, 2	.009.	
5	S. Andr	eas Meyer, 'Principle	s of Functional Verifi	cation'Newnes, 2003	3	

C	ategory	Programme core			
Cou	urse code	192VL22A			
Cou	ırse Title	Advanced VLSI De	sign Laboratory		
			Scheme a	and Credits	
Semester –II		L	Т	Р	Credits
		0	0	4	2
	Specificat	ion, Design, synthesi	s and layout design (floor planning, place	and route, power and
1	dock distr	ibution. clock tree sy	ynthesis, timing analy	vsis, power analysis,	signal integrity, post-
	layout sin	ulation and back ann	otation. GDS-II gene	ration) of digital buil	lding block.
Specification. Schematic Design, simulation. layout generation. Physical verification				cal verification (LVS.	
2	DRC. RC	extraction, post layout simulation, back annotation. GDS-II generation) of analog			
	building b	olock.			

Category Employability Enhancement Course							
Course	code	192VL25A					
Course Title		Industry Visit & Te	Industry Visit & Technical Seminar				
			Scheme a	nd Credits			
Semeste	er –II	L	Т	Р	Credits		
		0	0	4	2		
1 The student will make at least two technical presentations on current topics related to a specialization. The same will be assessed by a committee appointed by the department. The students are expected to submit a report at the end of the semester covering the variation aspects of his/her presentation together with the observation in industry visits. A q					t topics related to the by the department. The covering the various industry visits. A quiz		
	coverin	ng the above will be h	held at the end of the s	emester.			

SEMESTER III

Category		Employability Enha	Employability Enhancement Course					
Course code		192VL35A						
Course Title		Project Work-I						
			Scheme and	l Credits				
Semester –III		L	Т	Р	Credits			
		0	0	6	3			
1	Identific	cation of a real life pro	oblem in thrust area					
2	Develop	oing a mathematical m	nodel for solving the a	bove problem				
3	Finaliza	tion of system require	ements and specificati	on				
4	Proposing different solutions for the problem based on literature survey							
5	Future trends in providing alternate solutions							
6	Consoli	dated report preparati	on of the above					

SEMESTER IV

Category		Employability Enhancement Course				
Course co	ode	192VL45A	192VL45A			
Course Title		Project Work-II				
			Scheme and	d Credits		
Semester	–IV	L	Т	Р	Credits	
		0	0	28	14	
1	Cor	Consolidated report preparation of the above				
2	The (Blo	e project work involve Preparing a proje Problem identifie A statement of s ock Diagram/ Concep List of possible s Cost benefit anal Time line of acti	s the following ect :brief proposal ind cation ystem / process speci t tree) solutions Including al lysis vities	cluding fications proposed to lternatives and constr	be developed aints	
3	A re &st	eport highlighting the andards (if any))	design finalization (l	based on functional re	equirements	
4	A presentation Include the following Implementation phase(Hardware / Software / both) Testing and validation of the developed system Learning in the Project					
5		isonualed report prepa				

PROFESSIONAL ELECTIVE THEORY COURSES(Three to be opted for second semester)

Cat	egory	Professional Electiv	/e			
Cour	se code	192VL23A				
Cour	se Title	MIXED SIGNAL	VLSI DESIGN			
			Scheme a	nd Credits		
		L	Т	Р	Cred	its
	3 0 0 3					
Unit	-1	SWITCHED CAPACITOR C FILTERS				9
Univer amplif	rsal activ ïers - coi	e filter (KHN), Swit	ched capacitor filters old circuits - Biquad.	Switched capacitor	resistors - In	itegrator-
Unit	-2		ONTINUOUS TIME	FILTERS		9
Introdu –BiCN Eleme	uction to IOStrans	Gm - C filters - CM conductors - MOSFE asconductor building	OS Transconductors u T C Filters - Tuning (block- First and Second	sing Triode transisto Circuitry - Dynamic nd order filters.	ors, active tra range perfori	nsistors nance -
Unit	-3	DIGIT	AL TO ANALOG C	ONVERTERS		9
Non-ic	dealities	in the DAC - Types	of DAC's: Current s	switched, Resistive,	Charge redis	stribution
Unit	-4	ANAL	OG TO DIGITALCO	ONVERTERS		9
Types	of ADC	Cs- Flash, two step,	pipelined, successive	approximation, fol	ding ADC's.	SIGMA
DELT	A CON	VERTERS:Over sam	pled converters - ov	er sampling withou	t noise & w	ith noise
sigma	delta DA	C & ADC's. Non-ide	alities in the ADC.	cillation inters sec		louulatoi
Unit	-5	ANALOG AND	MIXED SIGNAL EX	XTENSIONS TO H	DL	9
Introdu Langu Interac Verilo Mixed	uction L age,Tole ction Qu g: Introd signal In	anguage design obje rance groups Conser iescent Point - Frequ uction data types -Ex nteraction.	ctives, Theory of dif vative systems Time lency domain model pressions – Signals, A	ferential algebraic e and the simulation ing and examples. analog behavior - Hi	equations, the cycle A/D Analog exteneration of the cycle A/D	e 1076.1 and D/A nsions to ructures -
			References			
1	Phillip <i>A</i> 2012.	Allen and Douglas Ho	lberg 'CMOS Analog	Circuit Design', Ox	ford Universi	ity Press,
2	Jacob Ba	aker, CMOS, Circuit	Design Layout and Sin	mulation , Wiley- IE	EE Press, 201	11.
3	David A 2008.	Johns and Ken Mar	tin, 'Analog Integrate	ed Circuit Design'. J	John Wiley a	nd Sons.
4	Benhard	Razavi, 'Data Conver	ters, Kluwer Publishe	rs, 2005.		
5	S. Kenn Publicat	eth S Kundert and ions, 2004.	Olaf Zinke, 'The De	signers Guide to V	erilog AMS;	Kluwer
6	Jacob E <u>Simula</u> ti	Baker, Harry W Li, on'. Wiley- <u>IEEE</u> Pres	and David E Boyo ss. 1998.	ce 'CMOS. Circuit	Design Lay	out and

Cat	Category Professional Elective					
Cour	se code	192VL23B				
Cour	se Title	VLSI SIGNAL PR	OCESSING			
			Scheme a	nd Credits		
		L	Т	Р	Cred	its
		3	0	0	3	
Unit	-1	REALIZA	TION OF DIGITAI	L FILTERS		9
FIR Fi	lter desig	n -IIR filter design -	Direct form I,II, Casc	ade, Parallel. Ladder	Lattice filter	s.
Unit	-2		ITERATION BO			9
Introd	uction, D	ata flow graph repres	entations, loop bound	and iteration bound,	Algorithms f	or
compu	ting Iter	ation bound, iteration	Bound of multirate E	Data - Flow Graphs.		0
	-5					
Introdu	uction Pi	pelining of FIR Digit	tal filters Parallel pro	cessing Pipelining a	nd parallel	
Unit	-4	TRA	NSFORMATIONS-	RETIMING		9
Introdu UNFC unfold Transf	uction - I DLDING: ing and r ormation	Definitions and Prope Introduction - An alg etiming -Application Register Minimization	rties Solving system of gorithm for unfolding of unfolding. FOLDI on Techniques - Regis	f Inequalities Retimi - Properties of unfol- NG: Introduction - fo ster Minimization in	ing Technique ding Critical j olding folded Archit	es. path, ectures
Unit	-5	0	FAST CONVOLUT	TION		9
Cook ' algorit archite	Toom alg hm, Algo ectures fo	orithm -modified Co orithmic strength redu r Rank-order filter.	ok - Toom algorithm '	Winogard algorithm- nsforms-parallel FIR	modified Wi	inogard lel
			References			
1	John G I and App	Proakis and Dimitris (lications Pearson, 20)	3 Manolakis, 'Digital 14.	signal processing - P	rinciples. Alg	;orithms
2	Uwe Me Springer	yer Sane, "Digital Sig , 2014.	gnal Processing with I	Field Programmable	Gate Arrays',	
3	Lonnie (C Ludeman, 'Fundame	entals of Digital Signa	l Processing', Wiley	India (P) Ltd	. 2010.
4	Peter Pir	sch 'Architectures for	Digital Signal Proces	ssing'. Wiley India (F	P) Ltd, 2009.	
5	Keshab I Wiley In	K Parhi. 'VLSI Digita ter science, 2007.	l Signal Processing S	ystems Design and I	nplementatio	n',

Category Professional Elective							
Cou	rse code	192VL23C					
Cou	rse Title	SEMICONDUCT	OR MEMORY DES	IGN AND TESTIN	G		
			Scheme a	nd Credits			
Seme	ester –II	L	Т	Р	Credi	dits	
		3	0	0	3		
Uni	t-1	RANDOM A	ACCESS MEMORY	TECHNOLOGIES		9	
Static MOS insula Speci Devel soft e DRAI	Static Random Access Memories (SRAM): SRAM cell structures. MOS SRAM Architecture. MOS SRAM cell and peripheral Circuit Operation. Bipolar SRAM Technologies, Silicon on insulator (SOI) Technology. Advanced SRAM Architectures and Technologies, Application Specific SRAMs. Dynamic Random Access Memories (DRAM): DRAM Technology Development CMOS DRAM, DRAM cell theory and advanced cell structures, BiCMOS DRAM, soft error failures in DRAM, Advanced DRAM Design and Architecture, Application Specific						
Uni	t-2	NC	ON-VOLATILE ME	MORIES:		9	
CMO time Techr Advar	S PROMS Program nology an nced Flash t-3	S, Erasable(UV) Prog mable EPROM (C d Architecture. Non Memory Architectu SEMICON	grammable ROM(EPF OTPEPROM), Elect volatile SRAM. Fla re, Content Addressal DUCTOR MEMOR	COM), Floating, Gate rically Erasable F ash Memories (EPR ble Memory. Y RELIABILITY	e EPROM Ce PROMS, EE COM or EEP	ll, One PROM ROM).	
Gener Relial Struct Uni t	ral Reliabi bility Mod tures-Relia t-4	lity Issues-RAM Fail eling and Failure Rat ability Screening and SEMICONDUC	ure Modes and Mech te Prediction-Design f Qualification.	anism Nonvolatile M or Reliability-Reliab	Iemory Reliat ility Test	oility-	
Radia Harde Hardr Struct	tion Effec ening Proc ness Assur	ts-Single Event Phen ess and Design Issue ance and Testing - R	omenon (SEP)•Radia s-Radiation Hardened adiation Dosimetry-W	tion Hardening Tech Memory Characteri Vater Level Radiatior	niques-Radiation stics-Radiation Testing and	tion n Test	
Uni	t-5	ADVANC	CED MEMORY TEC	CHNOLOGIES:		9	
Ferroe Memo Devic Testir	Ferroelectric Random Access Memories (FRAMs)-Gallium Arsenide (GaAs) FRAMs-Analog Memories- Magnetoresistive Random Access Memories (MRAMs)-Experimental Memory Devices. Memory Hybrids and MCMs (2D) -Memory Stacks and MCMs (3D).Memory MCM Testing and Reliability Issues-Memory Cards-High Density Memory Packaging Future Directions.						
			References				
1	Jesse Ru	ssell and Ronald Coh	n, 'Content-Addressal	ble Memory, Bookvi	ka Publishing	. 2012.	
2	Memorie	n, Masashi Horiguch s'. Springer. 2007.	i and Hitoshi Tanaka,	Ultra-Low Voltage	Inano-Scale		
3	Ashok K 2002.	Sharma. 'Semicondu	ctor Memories Techn	ology, Testing and R	Reliability', W	iley,	

4	Ashok K Sharma 'Advanced Semiconductor Memories - Architecture, Design and Applications, Wiley, 2002.
5	Betty Prince. 'Emerging Memories - Technologies and Trends, Kluwer Academic Publishers, 2002.

Cat	tegory		Professional Electiv	e				
Cour	se cod	e	192VL23D					
Cour	se Titl	e	VLSI TECHNOLO	DGY				
				Scheme a	nd Credits			
		-	L	Т	Р	Cred	its	
		-	3	0	0	3		
Unit	Unit-1 BASICS OF CRYSTAL GROWTH:						9	
Crysta	al struc	ture	- axes & planes. Cry	stal defects-Point def	ects & dislocations (Crystal growth	1-	
Bridg	man. C	zoc	hralski techniques &	Zone process.			0	
Unit	:-2		I	MATERIAL PROPH	ERTIES		9	
Dopin	g in the	e m	elt. Diffusion& ION	Implantation: Nature	of diffusion-interstit	tial Substituti	onal, tion D	
is con	stant &	osu fiir	nutional movements,	tems problems in Si	Diffusion Evaluation	n Techniques	Ion	
Impla	ntation	: Pe	enetration range, Imp	lantation Damage. Ar	nealing, Implantatio	on Systems.	1011	
Unit	:-3		OXIDA	TION & EPITAXY	OXIDATION		9	
Therm	nal Oxi	dati	on-Intrinsic, Extrins	ic silicon Glass, Oxid	e formation, Kinetic	s of Oxide gro	owth,	
Oxida	tion sy	ster	ns, Faults, Anodic O	xidation. EPITAXY:	Vapor Phase Epitax	y (VPE)- tran	sport,	
reaction	on and	gro	wth, Chemistry of gr	owth. Insitu etching.	Selective epitaxy. in	perfections.	Liquid	
Phase	Epitax	y. I	<u>LPE system, Evaluati</u>	on of epitaxial layers			0	
							9	
Uthog Ray E	raphyF Photo r	atte	ern generation & Ma	sking, Printing & Eng G: Wet chemical etcl	graving - Optical. E-l	Beam, 10n Bea	am. X-	
noncry	vstallin	e la	ms-Plasma etching,	Plasma-assisted etchi	ng, cleaning	nants, Etennig	5 101	
Unit	-5		DEVIC	F & CIDCUIT FAR	PICATION.		9	
Isolati	on- Me	esa.	Oxide. PN-iunction	isolations. Self Align	ment. Local Oxidation	on, Planarizat	ion.	
Metal	lizatior	n an	d Packaging. Circuit	s - N, P and CMOS T	ransistors. Memory	devices. BJT	- 7	
Circui	ts - Bu	ried	l Layer. PNP and NF	N Transistors, Diode	s, Resistors, Capacito	ors.		
				References				
1	Donal York,	d N Fot	eamen, DhrubesBisv arth edition, 2017.	vas, 'Semiconductor I	Physics and Devices'	McGraw Hil	t New	
2	Massi	mo	Ruden, ;Physics of	Semiconductor Devic	es, Springer, second	edition.2017		
3	Sze S	M,	'VLSI Technology, I	McGraw Hill, New Y	ork. second edition,	2017.		
4	Sorab Interso	K (Gandhi, 'VLSI Fabric ce Publications. Nev	ation Principles -Silio v York 2008.	con and Gallium Ars	enide'. Wiley		
5	Chang	g S `	Y and Sze S M "ULS	SI Technology". McG	raw Hill, New York	, 2007.		
6	Sze S	Ma	and Kwok K Ng ;Phy	vsics of Semiconducto	or Devices, John Wil	ey, 2006.		

Cate	tegory Professional Elective						
Cours	se code	192VL23E					
Cours	se Title	VLSI FOR WIRE	LESS COMMUNIC	ATION			
			Scheme a	nd Credits			
		L	Т	Р	Cred	its	
	3 0 0 3				3		
Unit-	Jnit-1 OVERVIEW OF MODULATION SCHEMES				9		
Classic Fading	cal Chanr Multipa	nel - Wireless Channe th Fading: Frequency	el Description - Path L Selective and Fast Fa	Loss - Channel Mode ading - Summary of S	l and Envelog Standard Tra	pe nslation	
Unit-	-2		RECEIVER FRON	T END		9	
Filter I Noise- Wideb Amplif	Design - Derivatio and LNA fiers - Po	Rest of Receiver Fro on of Noise Figure A - Design Narrowb wer Amplifiers	ont End: Non-idealitie e. AMPLIFIER DES oand LNA -Impedanc	es and Design Paran SIGN: Low Noise ce Matching - Auto	neters Nonlin Amplifier omatic Gain	earity - Design, Control	
Unit-	.3		TYPES OF MIX	ERS		9	
Balanc Low Fr Compl	ing Mixe requency ete Activ	er - Qualitative Descr Case: Analysis of G re Mixer, Switching N	iption of the Gilbert M ilbert Mixer - Distorti ⁄Iixer - Distortion in U	Aixer - Conversion C on - High-Frequency Jnbalanced Switchin	Gain - Distorti Case - Noise Mixer.	ion - e - A	
Unit-	-4	6	NOISE IN MIXE	ERS	0	9	
Conver Practic Sampli Sampli	rsion Ga al Unba ing Mixe ing Mixe	in in Unbalanced S lanced Switching M er - Distortion in Sin r Extrinsic Noise in S	witching Mixer Nois fixer. Sampling Mixe gle Ended Sampling fingle Ended Sampling	e in Unbalanced Sy er - Conversion Ga Mixer -Intrinsic No g Mixer- Demodulat	witching Mix in in Single vise in Single ors	cer - A Ended Ended	
Unit-	5	FR	EOUENCY SYNTH	ESIZERS		9	
Phase Digital Compl Design	Locked I Phase D ete Synt Approad	Loops - Voltage Cont Detectors - Frequency hesizer Design Exam Ches.	rolled Oscillators - Pl Dividers - LC Oscilla nple (DECT Applica	nase Detector - Analators -Ring Oscillato tion). Loop filter:G	og Phase Det ors - Phase No eneral Descr	ectors - oise - A iption -	
			References				
1	Luzzatto Wireless	A and Shirazi G. 'W Equipment and System	/ireless Transceiver I ems'. Wiley 2007.	Design: Mastering th	e Design of	Modern	
2	LaskarJ, and integ	ration", Wiley 2004	u Charaboly 5. Moc	iem receiver front e	aus.5ystems,	Circuits	
3	Bosco H	Leung 'VLSI for Win	reless Communication	ns, Pearson Education	n, 2002		
4	Leeneart 2002.	s D. Vander J Tang	and Vaucher C S 'Cin	rcuit design for RF	transceivers',	Springer	
5	S. Emad and Syste	N Farag and Moham ems. Kluwer Academ	ed I Elmasry, "Mixed nic Publishers, 2000.	Signal VLSI Wirele	ss Design Ci	rcuits	

Cat	egory	Professional Electiv	/e			
Cour	se code	192VL23F				
Cour	se Title	CPLD and FPGA	Architecture and Ap	plications		
			Scheme a	nd Credits		
		L	Т	Р	Cred	its
	3 0 0 3					
Unit	Unit-1 Introduction to Programmable Logic Devices					9
Introduction, Simple Programmable Logic Devices – Read Only Memories, Programmable Logic Arrays, Programmable Array Logic, Programmable Logic Devices/Generic Array Logic; Complex Programmable Logic Devices – Architecture of Xilinx Cool Runner XCR3064XL CPLD, CPLD Implementation of a Parallel Adder with Accumulation						
Unit	-2	Fie	eld Programmable G	ate Arrays		9
Organization of FPGAs, FPGA Programming Technologies, Programmable Logic Block Architectures, Programmable Interconnects, and Programmable I/O blocks in FPGAs, Dedicated Specialized Components of FPGAs, and Applications of FPGAs						
	-5				NOO MC2000	
Introd XC40	uction, Pr 00 Archit	ectures	ogy, Device Architect	ure, the Xilinx XC20	000, XC3000	and
Unit	-4	A	nti-Fuse Programme	d FPGAs		9
Introd Archit	uction, Pr ectures.	ogramming Technolo	ogy, Device Architect	ure, the Actel ACT1	, ACT2 and A	АСТЗ
Unit	-5		Design Applicati	ons		9
Genera Robot Adder	al Design Manipula s and Acc	Issues, Counter Exam ator, A Fast DMA Co cumulators with the A	nples, A Fast Video C ontroller, Designing C ACT Architecture.	Controller, and A Posounters with ACT de	sition Tracker evices, Design	for a ning
			References			
1	Stephen Internatio	M. Trimberger, "Fiel onal Edition.	d Programmable Gate	Array Technology"	, Springer	
2	Charles I	H. Roth Jr, LizyKuria	n John, "Digital Syste	ems Design", Cengag	ge Learning.	
3	John V.	Oldfield, Richard C.	Dorf, "Field Program	mable Gate Arrays",	Wiley India.	
4	Pak K. C Pearson	han/SamihaMourad, Low Price Edition.	"Digital Design Using	g Field Programmab	le Gate Array	'S'',
5	Ian Grou	t, "Digital Systems D	esign with FPGAs an	d CPLDs", Elsevier,	, Newnes.	
6	Wayne V Series.	Volf, "FPGA based S	ystem Design", Prent	ice Hall Modern Sen	niconductor D	Design

Cat	Category Professional Elective							
Cour	se co	de	192VL23G	192VL23G				
Cour	se Tit	tle	SYSTEM ON CH	IP DESIGN				
	Scheme and Credits							
			L T P Credi			its		
			3	0	0	3		
Unit	t-1			LOGIC GATES	6		9	
Introdu Gate C Interco	uction. Circuit	. Cor s. Lo t. Ob	nbinational Logic Fur w-Power Gates. Dela jectives	ctions. Static Complen ay Through Resistive Ir	nentary Gates. Switcl hterconnect. Delay Th	n Logic. Altern nrough Inductiv	ative ve	
Unit	t-2		COMBI	NATIONAL LOGI	C NETWORKS		9	
Introd	uctior	1. Sta	andard Cell-Based L	ayout. Simulation. Co	mbinational Networ	k Delay. Logi	c and	
interco	onnec	t De	sign. Power Optimiz	ation. Switch Logic N	etworks. Combination	onal Logic Te	esting.	
Unit	t -3			SEQUENTIAL MAC	CHINES		9	
Introd Syster	luctior n Des	ı. La ign	tches and Flip-Flops Power Optimization	. Sequential Systems Design Validation S	and Clocking Discip	lines. Sequen	tial	
Unit	t-4	-9		SUB SYSTEM DE	SIGN		9	
Introd	uction	ı. Su	bsystem Design Prir	ciples. Combinationa	l Shifters Adders A	LUs Multipl	iers	
High-	Densi	ty M	lemory. Field Progra	mmable Gate Arrays.	Programmable Logi	c Arrays. Ref	erences.	
Proble	ems.							
Unit	t-5			FLOOR-PLANN	ING		9	
Introd	uctior	ı, Flo	oor-planning Method	ls – Block Placement	& Channel Definitio	n, Global Ro	uting,	
switch	switchbox Routing, Power Distribution, Clock Distributions, Floor-planning Tips, Design							
Valida	Validation. Off-Chip Connections – Packages, The I/O Architecture, PAD Design.							
				References				
1	Wayr 2008	ne W	olf, "Modern VLSI De	sign – System – on – 0	Chip Design", Prentice	e Hall, 3rd Ed	tion,	
2	Wayr	ne W	olf , "Modern VLSI De	esign – IP based Desig	n", Prentice Hall, 4th	Edition, 2008		

Cat	tegory	Professional Electiv	/e			
Cour	se code	192VL23H				
Cour	se Title	MEMS AND NEM	IS			
			Scheme a	nd Credits		
		L	Т	Р	Credits	
		3	0	0	3	
Unit	-1	IN	TRODUCTION AN	D SCALING		9
MEMS and Microsystems development of MEMS technology- MEMS future and applications, Microsystems and microelectronics MEMS challenges - scaling - scaling in geometry, rigid body dynamics, electrostatic forces, electromagnetic forces, electricity, fluid mechanics, heat transfer.						
Unit	-2		MATERIALS FOR	MEMS:		9
Introd silicor arsenio	Introduction - substrates and wafer silicon substrate crystal structure, miller indices, properties silicon compounds silicon dioxide, silicon carbide, silicon nitride, polycrystalline silicon- gallium arsenide - quartz- piezoelectric crystals -polymers polymers for MEMS, conductive polymers.					
Physic	Physical Vapour Deposition (PVD), evaporation, sputtering, Chemical Vapour Deposition (CVD)					
etchin proces polish	g process ss wafer t ing - dopi	wet chemical etchin bonding - silicon fusi ing - diffusion, impla	g, plasma etching. Ior on bonding, anodic b nt.	n milling patterning onding- annealing- o	- lithography, chemical mec	, lift off chanical
Unit	-4	MEMS TH	CHNOLOGIES AN	D PACKAGING:		9
Bulk : compa proble packag	micromac arison of ems LICA ging post	chining Isotropic ar wet and dry etching Process and electro fabrication process,	nd anisotropic etching surface micromach oplating - Integration package selection, die	g. wet etchants. etc ining Introduction, of electronics and attach. Wire bond a	h stop, dry e process, ass MEMS techn nd Sealing.	etching, ociated nology-
Unit	:-5	HEMS TE	CHNIQUES AND A	PPLICATIONS:		9
Introd analys challe	uction to is and sir nges.	NEMS and its arch nulation - simulation	itecture carbon nano of Actuators, FET, Pr	tube electronics more e	deling -introc plications and	luction, d future
			References			
1	Anantha PA Ltd,	suresh G. K, Vinoy. I New Delhi, 2012.	K.J, Gopalakristman.S	, 'Micro and Smart S	Systems, Wile	ey India
2	Vijay K. Design a	Varadan, Vinoy. KJ, nd Development Met	Gopalakrishnan.S. "S hodologies, John Wil	Smart material System ey & Sons, New Yor	ns and MEM k. 2011.	S:
3	Tai Ran John Wi	Hsu. 'MEMS and Midley & Sons, New Jers	crosystems. Design. M ey. 2008.	Ianufacture and Nan	oscale Engine	eering.
4	James J Yolk 200	Allen, "Micro Electro)5.	Mechanical System	Design CRC Press-T	aylor & Franc	cis', New
5	Sergey E New Yor	dward Lyshevski. 'M rk. 2002.	EMS and NEMS syst	ems, Devices and St	ructures'. CR	C Press.

Cat	Category Professional Elective					
Cour	se code	192VL23I				
Cour	se Title	EMBEDDED SYS	TEM DESIGN			
			Scheme a	nd Credits		
		L	Т	Р	Credits	
		3	0	0	3	
Unit	-1	EMBEDI	DED DESIGN CYCI	LE OVERVIEW:		9
Differences between the Desktop PC and typical Embedded SystemExamples of Embedded Systems-Major hardware and software modules of an embedded system-Embedded Design Life Cycle. Introduction to ARM Controllers:ARMCortex-A. Cortex-R and Cortex-M series microcontrollers						
Unit	nit-2 INTRODUCTION TO PERIPHERALS 9					9
CPU Core, Program Memory. Data Memory, AHP and APB Bus Structure. System Peripherals: GPIO, Timers, EEPROM, Hibernation Module, WDT and DMA. Serial Peripherals: UART, I ² C, SPI, CAN and USB.						
Unit	Unit-3 PERIPHERAL INTERFACING TECHNIQUES:			9		
Analo Hardw Suppo	g Periph are and ort :JTAC	erals: ADC and Analo Software Interrupts, C 3 and BDM.	g Comparator. Motion Clock and Reset Gener	n Control Peripherals ator. Development a	s: PWM and and and debugging	QEI g
Unit	-4	PERIPHE	RAL PROGRAMM	ING TECHNIQUE	ES:	9
Host a Periph motors	ind Targ ierals, A s. interfa	et Machines. Configur nalog Peripherals and cing and Programmin	ing and Programming Motion Control Perip g Techniques.	of System Periphera herals. Display, Key	als, Serial board, Sensor	rs,
Unit	-5	REAL TIN	IE OPERATING SY	STEMS (RTOS)		9
Survey Data, I Interru	y of soft Message 1pt Rout	ware architectures. Tas Queues, Mailboxes a ines in RTOS Environ	sks and Task States, T nd Pipes, Timer functi ment.	asks and Data. Sema ions, Events, Memor	aphores and S y Manageme	bhared nt,
			References			
1	Steve F	urber, ARM System-o	n-Chip Architecture.	Prentice Hall of Indi	a. New Delhi	. 2009.
2	David E	E Simon, "An Embedd	ed Software Primer" I	Pearson Education A	sia. 2006.	
3	Arnold Technic	S. Berger, 'Embedded ues" CMP Books. 200	Systems Design:An I 02.	ntroduction to Proce	sses, Tools, a	nd
4	https:/w	ww.arm.com/products	s/processors			
5	https:/w	ww.ti.com/tiva				
6	https:/w	www.nordicsemi.com/	eng/Products/Nordic-'	Thingy-52		

Ca	tegory	y	Professional Electi	rofessional Elective				
Cou	rse co	de	192VL23J					
Cou	rse Ti	tle		ANALOG TO DIG	ITAL INTERFACE	ËS		
				Scheme a	nd Credits			
			L	Т	Р	Credits		
			3	0	0	3		
Uni	t-1		SA	MPLE AND HOLD	CIRCUITS		9	
Sampling switches, Conventional open loop and closed loop sample and hold architecture, Open loop architecture with miller compensation, multiplexed input architectures, recycling architecture switched capacitor architecture								
Uni	t-2		SWITCHED (SWITCHED CAPACITOR CIRCUITS AND COMPARATORS				
Switc feedb comp	hed-ca ack. S arator	apac Singl s.	itor amplifiers, swi e stage amplifier as	tched capacitor integ comparator, cascade	rator, switched capa d amplifier stages a	acitor commo s comparator	on mode , latched	
Uni	t-3		DIGIT	TAL TO ANALOG C	ONVERSION		9	
Perfo	rmanc	e me	etrics, reference mul	tiplication and division	on, switching and log	gic functions	in DAC,	
Resis	tor lad	lder	DAC architecture, cu	arrent steering DAC a	rchitecture.			
Uni	t-4		ANAL	OG TO DIGITAL C	ONVERSION		9	
Perfo	rmanc	e n Tir	netric, Flash arch	itecture, Pipelined	Architecture, Succe	essive appro	ximation	
Uni	t-5	, 111		PRECISION TECH	NIQUES		9	
Comp and d	oarator igital (r offs corre	set cancellation, Op	Amp offset cancellat	ion, Calibration tech	iniques, range	e overlap	
	References							
1	Behz 2000	zadR).	azavi, "Principles o	f data conversion sys	tem design", S. Cha	nd and comp	any Ltd,	

PROFESSIONAL ELECTIVE THEORY COURSES (Three to be opted for third semester)

	egory	Professional Electiv	/e				
Cour	se code	192VL33A					
Cour	se Title	HIGH SPEED DIG	GITAL DESIGN				
			Scheme a	nd Credits			
		L	Т	Р	Credits		
		3	0	0	3		
Unit	-1	TRANSM	IISSION LINES AN	D CROSSTALK		9	
Transmission line structures, signal propagation, transmission line parameters, line impedance,							
Propag capaci	gation de tance, cro	elay. Transmission	, minimizing cross tal	ross talk- Mutual k	inductance,	Mutual	
Unit	-2			TS		8	
Interco	onnect tec	chnologies, Multileve	l multilayer, interconr	nects, propagation de	lay. crosstalk		
analys Unit	analysis Unit 3 POWER and CLOCK DISTRIBUTION 10						
Locas	-J	1 for low impedance	nlangs and decoupling	appositors and their	coloction Ui	ah	
quality	y clock sig	gnals to components,	boards, and systems,	Common clock timi	ng and source	g11-	
synchr	ronous tin	ning			<u></u>	0	
	-4)	9	
of redu	ning for E	MC, EMC regulation reference in systems.	ns, typical noise path,	methods of noise co	upling, and m	nethods	
Unit	-5		GROUNDING	5		9	
Safety	grounds	signal grounds, sing	gle-point ground syste	ems, multi-point gro	und systems,	hybrid	
ground	ds, funct ding of ca	ional ground layou ble shields, ground lo	t, practical low free pops, shield grounding	quency grounding, at high frequencies	hardware g	rounds,	
8			References	<u> </u>	-		
1 Goel A K, "High speed VLSI interconnections' Wiley, 2007.							
1	UUEI A I	x, night speed vLSI	interconnections with	cy, 2007.)	
1 2	Paul CR:	Introduction to Elect	romagnetic compatibi	lity, Wiley 2006.)	
1 2 3	Paul CR: Howard	Introduction to Elect Johnson, Martin Graf	romagnetic compatibi nam. 'High speed Digi	lity, Wiley 2006. tal design. Pearson.	2005.)	
1 2 3 4	Paul CR: Howard Bogatin	Introduction to Elect Johnson, Martin Grab E, 'Signal integrity -s	romagnetic compatibi nam. 'High speed Digi implified', Prentice Ha	lity, Wiley 2006. tal design. Pearson. 2 all, 2003.	2005.)	
1 2 3 4 5	Paul CR: Howard Bogatin Hall S . I	Introduction to Elect Johnson, Martin Grab E, 'Signal integrity -s Hall G and McCall J,	romagnetic compatibi nam. 'High speed Digi implified', Prentice Ha " High speed digital s	lity, Wiley 2006. tal design. Pearson. 2 all, 2003. ystem design: AHan	2005. dbook of)	

Categ	gory	Professional Electiv	/e			
Course	code	192VL33B				
Course	Title	NANO SCALE DI	EVICES			
			Scheme a	nd Credits		
		L	Т	Р	Cred	its
		3	0	0	3	
Unit-1			OVERVIEW			9
Nano devices. Nano materials. Nano characterization-Definition of Technology node. Basic CMOS Process flow- MOS Scaling theory, Issues in scaling. MOS transistors: Short channel effects, Description of a typical 65 nm CMOS technology Requirements for Non-classical MOS transistor.						
Unit-2			MOS CAPACIT	OR		9
Role of interface quality and related process techniques, Gate oxide thickness scaling trend, Si02 vs. High-k gate dielectrics- Integration issues of high-k -Interface states, bulk charge, band offset. stability, reliability Qs, high field. Possible candidates. CV and IV techniques.						
Unit-3 METAL GATE TRANSISTOR					9	
Motivati ballistic integrati	Motivation, requirements, Integration Issues Transport in Nano MOSFET, velocity saturation, ballistic transport, injection velocity, velocity overshoot Ultrathin body 501 double gate transistors, integration issues – Vertical transistors – EinFET and Surround gate EET					
Unit-4	1	META	L SOURCE/DRAIN	JUNCTIONS:		9
Propertie function over Sili Compou structure	es of sc pinnin icon. PN ind sem MOSH	hotky junctions on Si g- Germanium Nano MOS versus NMOS. iconductors MOSFE ETs exploiting nove	licon, Germanium and MOSFETs: strain, qua Compound semicondu Ts in the context of ch I materials, strain, and	d compound semicor antization. Advantag actors material proper annel quantization a quantization.	nductors -Wo ges of German erties. MESFI and strain. He	rk iium ETs tero
Unit-5		SYNT	THESIS OF NANON	IATERIALS		9
CVD, Nucleation and Growth, ALD, Epitaxy, MBE. Compound semiconductor hetero-structure growth and characterization Quantum wells and Thickness measurement techniques -Contact - step height. Optical - reflectance and ellipsometry.AEM. Characterization techniques for nanomaterials: FTIR. XRD, AFM. SEM, TEM, EDAX etc-Applications and interpretation of results. EMERGING NANO MATERIALS: Nanotubes, nanorods and other Nano structures. LB technique. Soft lithography. Microwave assisted synthesis. Self assembly. References 1 Karl Goser, Nanoelectronics and Nanosystems: From Transistors to Molecular and Quantum Devices. Springer. 2005.						
$\begin{array}{ c c } 2 & M \\ M \end{array}$	aserRa	and Novel Devices,	Wiley-VCH, 2005.	recinology (Ad		curome

Cat	egory	Professional Electiv	ve				
Cour	se code	192VL33C					
Cour	se Title	MODELING AND	SIMULATION OF	NANOSCALE TR	ANSISTOR	S	
			Scheme a	nd Credits			
		L	Т	P Credi		its	
		3	0	0	3		
Unit	-1	Α	NALYTICAL MOD	ELLING		9	
Introduction - Types of Models - Attributes of Good Compact Models - Model Formulation - Model Implementation in Circuit Simulators Model Testing - Parameter Extraction - Simulation and Extraction for RF Applications. Analytical Solution Methods: Parabolic Approximation Variable Separable Numerical Simulation Fourier series - Green Function -Bessel Function.							
Unit	-2	TECHNOLO	GY-ORIENTED CA	AD & DEVICE CA	D	9	
Intro	Introduction - Process and Device CAD - Process Simulation Techniques -Interfaces in process						
unit	Unit-3 DEVICE CAD - CMOS Technology - Ion Implantation - Oxidation - Impurity Diffus			purity Diffus	ion. 9		
Semic	Semiconductor Device Analysis - The PN Junction - Equilibrium Conditions - Non-equil			librium			
Conditions - Bipolar Junction Structures, Carrier Densities - Carrier Transport and Conversation -							
Field-l	Effect St	ructures. The MOS	capacitor - Basic M	OSFET I-V Charact	teristics - Th	reshold	
Voltag	pe in Non	uniform Substrate - N	AOS device Design by	Simulation		lesitora	
Unit	-4		TCAD SIMULAT	TION		9	
Proces	ss simulat	or - Device simulato	r - Advanced concept	s - drift-diffusion, h	ydrodynamic	model,	
stress simula	models S ation Elec	tructure editor meshi tromagnetic simulation	ing concepts - work b on.	ench - Plotting - Sc	ripting -Mon	te-carlo	
Unit	-5	NOVEL	TRANSISTOR ARC	CHFIECTURES		9	
Nanov electro Electro	vire trans on transis on wave t	sistor - High electro tor - Carbon nanotu ransistor Electron spi	n mobility transistor be transistor - Doubl in transistor.	Tunnel field effect e gate and multi ga	t transistor - te MOS tran	Single sistor -	
			References				
1	Robert V Devices.	V.Dutton and Zhiping Springer, 2012.	yYu, 'Technology CA	D Computer Simula	tion of Proces	sses and	
2	Rainer W and Nov	Vaser. 'Nanoelectronic el Devices'. 3rd Edition	cs and Information Te on. Wiley VchVerlag,	chnology: Advanced Weinheim, 2012.	l Electronic N	Iaterials	
3	YannisT Edition,	sividis and Colin Mc. Oxford University Pr	Andrew, 'Operation an ess, 2011	nd Modeling of the N	AOS Transist	or, 3rd	
4	Mark S. Simulati	Lundstrom and Jing (on, Springer. 2006	Guo, 'NanoscaleTrans	istors:Device Physic	s. Modeling a	und	
5	ShunriO	da and David Ferry,'S	SiliconNanoelectronic	st CRC Press, New Y	York, 2005.		
6	Karl Go Springer	olser, Peter Gloseko . 2004.	tter and Jan Dienst	uhl, ⁻ Nanoelectroni	cs and Nan	osystems	

Cat	ntegory Professional Elective							
Cour	rse cod	le	192VL33D					
Cour	rse Tit	le	ADVANCED O PROCESSING	COMPUTER	ARC	CHITECTURE	AND PAH	RALLEL
				Sch	eme a	nd Credits		
			L	Т		Р	Credits	
			3	0		0	3	
Unit	t-1		INTROD	UCTION TO I	PARA	LLELPROCESSIN	NG	9
Evolution of computer systems.Generation of computersystemsTrendstowardsparallelprocessingParallelprocessing mechanisms parallelComputerstructureArchitectural classification schemes Application						systems structure		
Unit	t-2		MEMORY AND I/O SUBSYSTEMS, PIPELENING					9
alloca proces Desig	allocation and management - I/O subsystems pipelining: Principles - Classification of pipeline processors -Reservation tables - Interleaved memory organization - Design of arithmetic pipeline - Design of instruction pipeline.							
Unit	t-3		VECT	OR AND ARE	RAY P	ROCESSING		9
Need optim netwo	- Bas izatior orks - F	ic v 1 m Paral	ector processing ar ethods. Array pro- lel algorithms for ar	chitecture - Iss cessing: SIMD ray processors -	sues in Arra - assoc	vector processing y processors - SI iative array processi	- Vectorizat MD intercor	ion and inection
Unit	t -4		MULT	IPROCESSO	RARC	HITECTURE	0	9
Functi concu	ional s rrency	truc for	tures - Interconnect multiprocessing	ion network - N	Aulti c	ache problems and	solutions -Ex	ploiting
Unit	t-5		PRINCIPLES	OF PARALL	EL AI	GORITHM DESI	GN	9
Desig paralle MIMI	n appr el algo D algo	oach orith rithn	nes-Design issues-Pe ms - Pseudo code c ns.	erformance mea conventions for	asures parall	and analysis-Compl el algorithms-Comp	exities-Anom arison of SIN	alies in MD and
				Refere	nces			
1	Kai I Progr	Hwa amn	ng, NareshJotwani: nability, Tata McGra	Advanced Co aw Hill, 2011	mpute	r Architecture - Pa	arallelism, So	calability,
2	John 2011.	LH	ennessy, "Computer	Architecture a	Quanti	tative Approach", H	arcourt Asia	Pvt. Ltd.,
3	Seyec	lRoc	osta, Parallel Process	sing and Paralle	l Algo	rithms", Springer Se	eries, 2000.	

Categ	gory	Professional Electiv	ve			
Course	e code	192VL33E				
Course	Title	ADV	ANCED DIGITAL	IMAGE PROCESS	SING	
			Scheme a	nd Credits		
		L	Т	Р	Credi	its
		3	0	0	3	
Unit-1		FUNDAMENTA	LS OF DIGITAL I	MAGEPROCESSI	NG	9
Element	s of ima	age perception, Brigh	tness, Contrast, Hue,	Saturation, Match Ba	and Effect, 2I) image
Unit-2	Unit-2IMAGE ENHANCEMENT9					9
Spatial Fi Using Ari Frequenc Homomor	Spatial Filters: Point processing, Some Basic Gray Level Transformations, Histogram Processing, Enhancement Using Arithmetic/Logic Operations, Basics of Spatial Filtering, Smoothing Spatial Filters, Sharpening Spatial Filters Frequency Domain Filters: Smoothing Frequency-Domain Filters, Sharpening Frequency Domain Filters, Homomorphic Filtering					
Unit-3		I	MAGE SEGMENTA	ATION		9
Edge Link Merging, 2 RGB Vect	king and l Dam Cor tor Space	Boundary Detection, Thro astruction, Watershed Seg , Color Edge Detection	esholding, Basic Formulat gmentation Algorithm, Seg	ion, Region Growing, Re gmentation in HSI Color	egion Splitting a Space, Segmen	nd tation in
Unit-4		IMAGE RESTORA	ATION AND COLO	R IMAGE PROCE	SSING	9
Image Deg (Wiener) I Color Seg	gradation Filtering, gmentatio	/Restoration Process, No Color Fundamentals, Co n	ise Models, Mean Filters, lor Models, Pseudocolor I	Inverse Filtering, Minim mage Processing, Smoot	um Mean Squar hing and Sharpe	e Error ning,
Unit-5		IMAGE CON	IPRESSION AND F	REPRESENTATIO	N	9
Coding Re Decoder, ' Theorems on Decisio	edundanc The Char , Using In on-Theor	y, Interpixel Redundancy inel Encoder and Decode nformation Theory, Repr etic Methods	 Psychovisual Redundan r, Measuring Information, esentation, Boundary Desc 	cy, Fidelity Criteria , The The Information Channe criptors, Regional Descri	e Source Encode el, Fundamental ptors, Recogniti	r and Coding on Based
			References			
1 G	onzalez	and Woods, Digital	Image Processing, Pr	entice-Hall.		
2 A 19	K. Jair 989.	n, "Fundamentals of I	Digital Image Process	ing", Prentice-Hall, A	Addison-Wes	ley,
3 J.	C. Rus	s. The Image Process	ing Handbook. CRC,	Boca Raton, FL, 4th	edn., 2002.	
4 W	V. K. Pr	att. Digital image pro	cessing, PIKS Inside.	Wiley, New York, 3	Brd, edn., 200	1.

Ca	tegory	Professional Electiv	/e			
Cou	rse code	192VL33F				
Cou	rse Title		SELECTED TOPI	CS IN IC DESIGN		
			Scheme a	nd Credits		
		L	Т	Р	Credits	
		3	0	0	3	
Uni	t-1	VOLTAG	E AND CURRENT	REFERENCES		9
Curre	nt Mirrors	, Self Biased Current	Reference, startup ci	rcuits, VBE based C	urrent Reference	e, VT
Based	l Current I	Reference, Band Gap	Reference, Supply Ir	ndependent Biasing,	Temperature	
Indep	endent Bia	asing, PTAT Current	Generation, Constant	Gm Biasing	1	
Uni	t-2	LOV	V DROP OUT REGU	JLATORS		9
Gener	ral layout a	and construction cons	sideration, Output Vol	ltage Accuracy, Desi	gn issues and g	general
applic	cations			•		
Uni	Unit-3OSCILLATOR FUNDAMENTALS9			9		
Gener	General considerations, Ring oscillators, I.C. oscillators, Colnitts Oscillator, litter and Phase noise in					
Ring	Oscillators	s. Impulse Sensitivity	Function for Ring Os	scillators. Phase Nois	se in Differenti	al LC
Oscill	lators.	, I	6	· · · · · · · · · · · · · · · · · · ·		
Uni	t-4		PHASE LOCK LO	OPS		9
PLL	Fundamen	tal. PLL stability. No	ise Performance. Cha	rge-Pump PLL Topo	ology, CPPLL	
Build	ing blocks	Jitter and Phase No	ise performance.	-80 - 0mp - 22 - op o		
Uni	t-5	CLC	CK AND DATA RE	COVERY		9
CDR	Architectu	res Tias and Limiter	rs. CMOS Interface. I	inear Half Rate CM	OS CDR Circu	its
Wide	capture R	ange CDR Circuits.	,		02 02 11 011 0	,
	1		References			
1	BehzadR 2003.	azavi, "Design of Int	egrated circuits for O	ptical Communicatio	ons", McGraw I	Hill,
2	Floyd M	Gardner,"Phase Lo	ck Techniques" John	wiley& Sons, Inc 20	05.	
3	Gabriel. bandgapo	A. Rincon-Mora, "Vo circuits",Johnwiley&	ltage references from Sons, Inc 2002.	diode to precision hi	gher order	
4	MichielS Circuit D Managen	teyaert, MichielSteya Design - High Speed Conent "springer, 2008	aert, Arthur H.M. van Clock and Data Recov 3.	Roermund, Herman ery, High-performan	Casier "Analogice Amplifiers	g Power

Catego	ry	Professional Electiv	rofessional Elective					
Course c	ode	192VL33G						
Course T	itle	ELECTRONIC PA	ACKAGING TECH	NOLOGIES				
			Scheme a	nd Credits				
		L	Т	Р	Cred	its		
		3	0	0	3			
Unit-1		OVERVIEW OF	FELECTRONIC SY	STEMS PACKAG	ING:	9		
Packaged aspects of	Packaged Electronics - Technologies- Trends- Products and levels of packaging- Packaging aspects of handheld products.							
Unit-2		BASICS O	BASICS OF SEMICONDUCTOR PACKAGING:					
Basics of Semiconductor and Process flowchart; Wafer packaging; Packaging evolution- Chip connection choices -Wire bonding, TAB and flip chip, Single chip packages or modules (SCM).								
Unit-3		TYPES OF PACKAGING 9						
Commonly Thermal n System-in	y usec nisma packa	l packages and advar tch in packages; Curr age(SIP)- Packaging	nced packages; Materi rent trends in packagin roadmaps- Hybrid cir	als in packages- Adv ng-Multichip module cuits.	vances packag es (MCM)-typ	ges bes;		
Unit-4		ELECTRICAL	DESIGN CONSIDER PACKAGING	RATIONS IN SYST	EMS	9		
Electrical the Reflec	Issues tion p	s - Resistive Parasitic roblem-Interconnect	- Capacitive and Induion.	active Parasitic- Lay	out guidelines	s and		
Unit-5		THERMAL	MANAGEMENT A	ND RELIABILITY	:	9		
Heat-trans radiation- and fatigue	fer fu Cooli e.	ndamentals Thermang -Reliability- Basi	al conductivity and res c concepts- Environm	sistance- Conduction ental interactions- Tl	, convection a hermal misma	and atch		
			References					
1 Rac	R Tu	ummala, "Fundament	als of Microsystems I	Packaging", McGraw	Hill, NY, 20	01		
2 Wil	liam	D Brown, "Advanced	l Electronic Packaging	g", IEEE Press, 1999				

Ca	tegory	Professional Elective				
Cou	rse code	192VL33H				
Cou	rse Title	VLSI FOR IoT SY	STEMS			
			Scheme a	nd Credits		
		L	Т	Р	Credits	
		3	0	0	3	
Uni	t-1	<u> </u>	INTRODUCTIC	N		9
Conc Key f techno	cept of con features of ology - ex	nected world - Need, loT architecture, Mea amples	Legacy systems for c rits and Demerits of lo	connected world - fea oT technology, Appl	atures and lim ications drive	iitations, n by loT
Uni	l-2		COMPONENTS O	F IoT		9
Review of classic embedded system architecture, Basic building blocks of anIoT system - Artificial Intelligence, Connectivity, Sensors and Computing nodes. Sensors used in IoT systems - Characteristics and requirements, Types of sensors for IoT systems, Compute nodes of IoT, Connectivity technologies in IoT - Software in IoT systems - features and properties.						
	1-5					,
Memo Out R IC's a Unit Electr DSPs hardw	ories, Anti Regulators, and System t-4 ronic Syst and FPG vare system	-Fuse One Time Prog DC-to-DC Converter s, Role of Field Prog ELECTH em Design for loT - A's, System Power ns, Form Factor - Gu	grammable (OTP) me ers, Voltage Reference rammability in loT sy RONIC SYSTEM DE Requirements, Com Supply Design for lo idelines and prevailin	mories, Power Managem es, Power Managem estems. CSIGN FOR IoT puting blocks in lo' oT systems, Mixed a g standards.	agement - Lov ent Units (PM T systems - I Signal challes	w Drop (IUs) in 9 MCU's, nges in
Uni	t-5	ELECTRON	IC SYSTEM DESIG	GN CHALLANGES	5	9
Comp Opera issues	oonent mo ating cond s, EMI/EM	dels & System Des itions of loT devices IC, SI/PI and Reliabil	ign - Feasibility and and impact on Electi ity Analysis in loT sy	l challenges, System ronic System Design rstems.	n Level Integ ; Hardware S	gration, Security
			References			
1	Alloto, " Springer	Enabling the Internet Publications, First Ed	of Things- From Inte dition, 2017.	grated Circuits to Int	tegrated Syste	ems",
2	Pieter Ha the loT, a Publishir	rrpe, Kofi A. A. Mak and Sub-1V & Advan ng AG, 2017	inwa, Andrea Baschir ced Node Analog Cir	otto, "Hybrid ADCs, cuit Design", Spring	, Smart Senso er Internation	rs for al
3	Rashid K and Elect	han, KajariGhoshdas tron", Packt Publishir	tidar, AjithVasudevan 19 Limited (Verlag), 2	n, "Learning loT with 2016.	h Particle Pho	oton
4	ApekMu Revolutio	lay, "Sustaining Moo on" Morgan and Clay	re's Law: Uncertainty pool Publishers, 2015	Leading to a Certain	nty of loT	
5	OrCAD, https:/wv	"P-spice Technology vw.pspice.com/soluti	for Internet of Thing on/pspice-technology	s" - -internet-things		
6	Jim Lipn Application	nan, Sidense Corp." N ions"- https:/www.de ons.html	IVM memory: A Crit sign-reuse.com/article	ical Design Consider es/32614/nvm-memo	ration for loT ory-iot-	

Ca	tegory	Professional Electiv	Professional Elective				
Cou	rse code	192VL33I					
Cou	rse Title	Quantum Dot Cell	ular Automata Nano	o Technology			
			Scheme a	nd Credits			
		L	Т	Р	Credits		
3 0 0 3							
Uni	t-1		INTRODUCTI	ON		9	
Emer	Emerging Nanotechnologies- Electronics beyond Moore's law - Limitations of CMOS technology-						
Alteri	natives to	MOSFET and Challe	nges - Emerging Tran	sistor Based Devices	s-IC Technolo	ogy	
beyor	nd CMOS	Era- USDM and Qua	intum computing-QCA	A modeling approach	1.		
Uni	t-2			0.01		9	
001	Desias	Calmadin carla a such	QCA TERMINOL	<u>OGY</u>	Non Toro		
QCA	Basics -	Schrödinger's equation	on in quantum wires	s - Quantum boxes	- Non-zero	angular rhitrory	
shape	-Approx	ches to pyramidal	dots- Matrix appr	n uois- Cubondar uo	hrough dot	arrave-	
Cross	\sim -Appilo	CA -Convergence te	sts- Efficiency- Tool t	for OCA Simulation	inougn dot	allays-	
Lini	t_3	RA	SIC COMPONENT			9	
	1-5	DA)	
Logic	Primitive	es in QCA- Clockir	ig in QCA - Role a	nd Types -Design	of Logic Ga	tes and	
Multi	plexer in (QCA - Design of a O	ne-Bit Full-Adder - F	lip-Flop in QCA. Ac	ders and Mu	ltipliers	
In QC	CA						
Uni	t-4	DESIGN	OF DIGITAL CIR	CUITS IN QCA		9	
Desig	n of Ripp	le Carry Adder (RCA	A) and Prefix Adders	in QCA- Design of	16-Bit Hybrid	l Adder	
in QC	CA- Layou	it Level Implementat	tion of adders and Co	omparisons. Introduc	ction to Multi	pliers -	
Desig	n of a Mu	ultiplier in QCA - Th	ne Baugh - Wooley N	Aultiplier for 2's Co	mplement Nu	imbers-	
Desig	n of Baug	h-Wooley Multiplier	in QCA.				
Uni	t-5		TRANSFORM IN	QCA		9	
Discr	ete Hadan	nard Transform Com	putation in QCA - B	asics of Discrete H	adamard Trar	nsform-	
Mathe	ematical I	Formulation for DH	Γ Computation- QCA	A Realization - Per	formance of	a Full-	
Parall	el Additic	on Strategy - Applicat	ions of Quantum Dot	Cellular Automata 7	Fechnology.		
			References				
1	Paul Har	rison, Alex Valavani	s -Quantum Wells, W	ires and Dots: Theor	etical and		
1	Computa	tional Physics of Sen	niconductor Nanostru	ctures, 4th Edition, V	Wiley, April 2	016.	
	K. Sridh	aran, VikramkumarF	Pudi -Design of Arith	metic Circuits in Q	Quantum Dot	Cellular	
2	Automat	a Nanotechnology	Studies in Computat	tional Intelligence-S	Springer Inte	rnational	
	Publishir	ng-2015.					
3	Fabrizio	Lombardi, Jing Huar	ng - Design and Test o	f Digital Circuits by	Quantum-Do	ot	
	Cellular	Automata-Artech Ho	use-2007.				
4	Kasper, l	E., Paul, D -Silicon Q	uantum Integrated Ci	rcuits -Silicon-Germ	anium		
Ľ	Heterosti	ructure Devices: Basi	cs and Realisations-S	pringer-Verlag Berli	n Heidelberg	2005.	
5	Paul Har	rison, Alex Valavani	s -Quantum Wells, W	ires and Dots: Theor	etical and	0.4.5	
	Computa	tional Physics of Sen	niconductor Nanostru	ctures, 4th Edition, V	Viley, April 2	016.	
_	K. Sridh	aran, VikramkumarF	Pudi -Design of Arith	metic Circuits in Q	Quantum Dot	Cellular	
6	Automat	a Nanotechnology	Studies in Computat	tional Intelligence-S	Springer Inte	rnational	
	Publishir	ng-2015.					

Category		Professional Elective					
Course code		192VL33J					
Course Title		Genetic Algorithms for VLSI Design					
		Scheme and Credits					
		L	Т	Р	Credits		
		3	0	0	3		
Uni	t-1	GA OPER	ATORS AND GA F	ORALGORITHM		9	
Introduction, GA Technology-Steady State Algorithm-Fitness Scaling-Inversion							
Unit-2					9		
GA for VLSI Design, Layout and Test automation-partitioning- automatic placement, routing							
technology, Mapping for FPGA -Automatic test generation-Partitioning algorithm Taxonomy -							
Unit-3		GA FOR PARTITIONING,PLACEMENT AND ROUTING				9	
IIvha	d constis	genetic encoding local improvement WDEP Comparison of Cas Standard					
cell placement-GASP algorithm-unified algorithm.							
Unit-4		AUTOMATIC TEST GENERATION				9	
Global routing-FPGA technology mapping-circuit generation-test generation in a GA frame							
work-test generation procedures.							
Unit-5		PEAK POWER ESTIMATION AND PARALLEL IMPLEMENTATIONS				9	
Power estimation-application of GA-Standard cell placement-GA for ATG-problem							
encoding- fitness function-GA vs Conventional algorithm.							
References							
1	PinakiM Automat	kiMazumder, E MRudnick, "Genetic Algorithm for VLSI Design, Layout and test omation", Prentice Hall, 1998					
2	Randy L	L Haupt, Sue Ellen Haupt, "Practical Genetic Algorithms", Wiley-Interscience,2004.					
3	Ricardo Maria Be and Syste	rdo Sal Zebulum, Macro Aurelio Pacheco, Marley Maria B R Vellasco and Marley ia Bernard Vellasco, "Evolution Electronics: Automatic Design of Electronic Circuits Systems Genetic Algorithms", CRC press, 2001					
4	John R K Automat	nn R Koza, Forrest H Bennett ID, David Andre and Morgan Kufmann, "Genetic tomatic Programming and Circuit Synthesis", 1999					